

808 nm High-Power Laser Diode (AL0808T500)

Features:

Output power: 0.5w(CW)
 Variety of stripe width
 Efficient quantum well structure

Application:

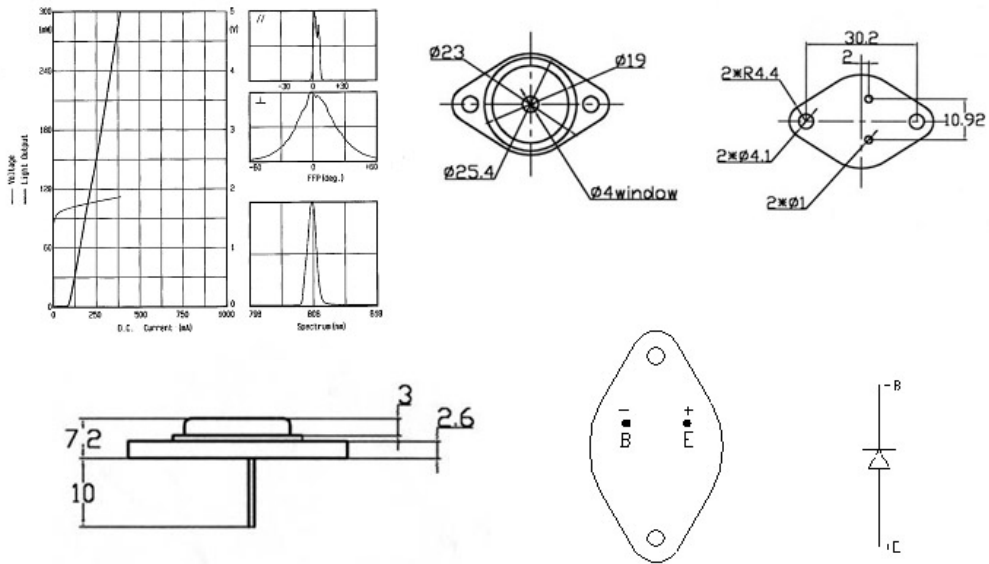
Solid-state laser pumping
 Medical usage
 Beacons and Illumination
 Free-space communication
 Infrared light sources



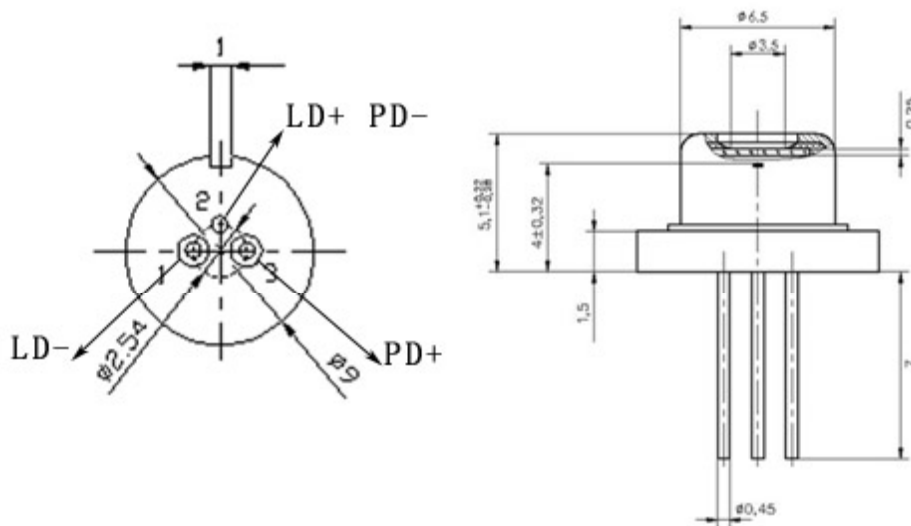
Specifications:

Parameter	Value
	AL808T500
CW output power (mW)	500
Peak wavelength (nm)	808 ± 3
Spectral width (nm)	≤ 5
Threshold current (A)	≤ 150
Operating current (A)	≤ 650
Operating voltage (V)	1.6 ~ 2.2
Operating Temperature	$-10 \sim 50^{\circ}\text{C}$
Storage Temperature	$-40 \sim 85^{\circ}\text{C}$
Slope efficiency (W/A)	≥ 0.9
Beam divergence $\theta_{\perp} \times \theta_{\parallel}$ (deg.)	12/40
Wavelength temperature coefficient (nm/ $^{\circ}\text{C}$)	0.3
Emitting area (μm)	50×1
Serial resistance (Ω)	≤ 1.5
Lifetime(h)	10000
Package	TO-5, TO-3, C-Mount

TO-3 Package(Unit: mm)

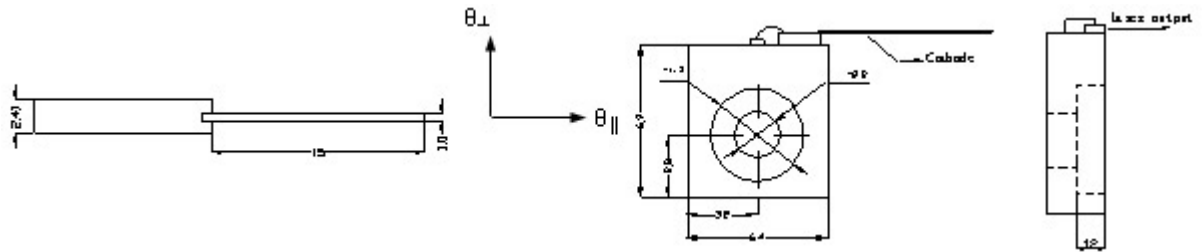


TO-5 Package: (Unit: mm)



-Mount heat sink: (Unit : mm, Heat sink(+))

C-Mount 1 (C)



C-Mount 2 (S)

